

In the Abstract:

Please rewrite the abstract as follows:

~~The invention relates to a~~ A nonvolatile memory cell, memory cell arrangement, and method for production of a nonvolatile memory cell is disclosed. The nonvolatile memory cell ~~comprises~~ includes a vertical field-effect transistor (FET), ~~with~~. The FET contains a nanoelement arranged as a channel region and an electrically insulating layer. The electrically insulating layer at least partially ~~surrounding~~ surrounds the nanoelement and acts as a charge storage layer and as a gate-insulating layer. The electrically insulating layer ~~above~~ is arranged such that electrical charge carriers may be selectively introduced into or removed from the electrically insulating layer ~~above~~ and the electrical conductivity characteristics of the nanoelement may be influenced by the electrical charge carriers introduced into the electrically insulating layer.